CLAIM AMENDMENTS

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L Courrently omen	dad) An an ahi	n inductor	COncieting (\+ •
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at least one a dielectric layer;

at least one a conductive winding on the at least one dielectric layer; and

a P-well having a major surface parallel to a major surface of the dielectric layer; and

a substrate having a major surface parallel to the major surface of the dielectric layer.

2. (currently amended) The on-chip inductor of claim 1 further consists of An on-chip inductor consisting of:

a dielectric layer;

a conductive winding on the dielectric layer;

a P-well having a major surface parallel to a major surface of the dielectric layer;

a field oxide having a major surface that is juxtaposed to the major surface of the P-well; and

a substrate having a major surface parallel to the major surface of the dielectric layer.

3. (currently amended) The on-chip inductor of claim 1 further consists of wherein:

the at least one dielectric layer including one layer; and

the at least one conductive winding including is a spiral winding on the one layer.

- 4 8. (canceled).
- 9. (currently amended) An on-chip inductor consisting of:
- at least one a dielectric layer;
- at least one a conductive winding on the at least one dielectric layer; and
- <u>a</u> field oxide layer having a major surface parallel to a major surface of the dielectric layer; and
- a substrate having a major surface parallel to the major surface of the dielectric layer.
- 10 -30. (canceled)